

## Diode DC forward characteristic SPICE parameter extraction.

The DC forward characteristic  $V_d=f(I_d)$  of a diode is typically described by the following equation:

$$V_d = I_d \times R_s + N \times \frac{k \times T}{q} \ln \left( \frac{I_d}{I_s} + 1 \right) \quad (1)$$

$\frac{k \times T}{q}$  is the electron temperature  $V_e$

The following parameters must be found:

$R_s$  Diode series resistance  
 $N$  Emission coefficient.  
 $I_s$  Saturation current.

To calculate the there parameters we need two measurements with very low diode currents to eliminate the effect of the diode series resistance.

The diode series resistance can be calculated if we have found the  $N$  and  $I_s$  parameter using one measurement with a very high diode current. This is because now the series resistance has a significant effect on the diode forward voltage.

First for  $N$  and  $I_s$  we need the two very low values for  $I_d$  and  $V_d$  so we can simplify the basic diode equation solve the two for  $N$  and put the two together to solve  $I_s$ .

$$\begin{aligned} V_{d1} &= N \times \frac{k \times T}{q} \ln \left( \frac{I_{d1}}{I_s} \right) & V_{d2} &= N \times \frac{k \times T}{q} \ln \left( \frac{I_{d2}}{I_s} \right) \\ \frac{V_{d1}}{\frac{k \times T}{q} \ln \left( \frac{I_{d1}}{I_s} \right)} &= \frac{V_{d2}}{\frac{k \times T}{q} \ln \left( \frac{I_{d2}}{I_s} \right)} \\ I_s &= I_{d2} \left( \frac{I_{d2}}{I_{d1}} \right)^{\frac{V_{d2}}{V_{d1}-V_{d2}}} \end{aligned} \quad (2)$$

The  $N$  parameter can now be calculated using equation (1) without the  $R_s$ :

$$N = \frac{V_{d1}}{\frac{k \times T}{q} \ln \left( \frac{I_{d1}}{I_s} + 1 \right)} \quad (3)$$

The parameter  $R_s$  must be calculated using one  $V_d$  value with measured with a very high diode forward current using equation (1)

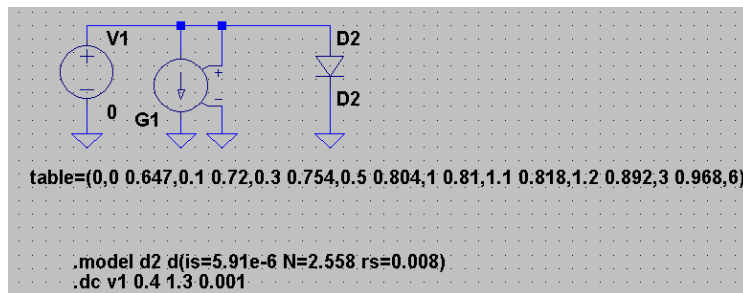
$$V_d = I_d \times R_s + N \times \frac{k \times T}{q} \ln\left(\frac{I_d}{I_s} + 1\right) \quad R_s = \frac{V_{d3} - N \times \frac{k \times T}{q} \ln\left(\frac{I_d}{I_s} + 1\right)}{I_{d3}} \quad (4)$$

### Example using the BYV29

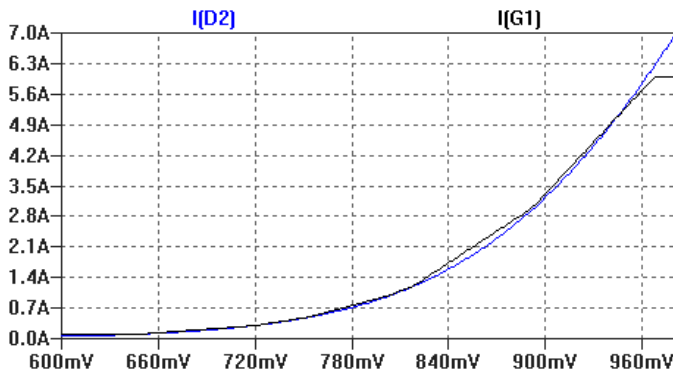
From the dc diode characteristics only high values for  $I_d$  and  $V_d$  could be read from the data sheet so practical measurements with a current source and voltmeter were used to measure the required low  $I_d$  and  $V_d$  values. The values are:

Dc characteristics			
	$V_d$	$I_d$	
1	0.647	0.100	A
2	0.72	0.300	A
3	0.97	6.000	A

More values were measured and put in a spice test circuit:



Simulation results showing the measured and simulated  $I_D$  vs  $V_d$ :



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